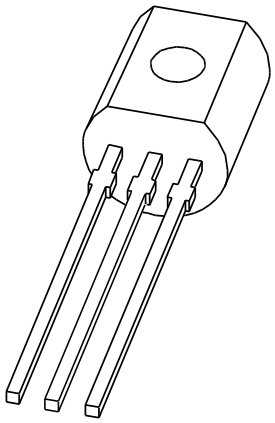
DATA SHEET



BC635; BC637; BC639
NPN medium power transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Mar 12

Philips
Semiconductors

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NPN medium power transistors BC635; BC637; BC639

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

- Driver stages of audio/video amplifiers.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.
PNP complements: BC636, BC638 and BC640.

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter

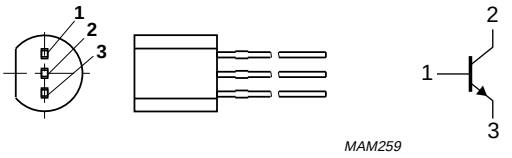


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC635		–	45	V
	BC637		–	60	V
	BC639		–	100	V
V_{CEO}	collector-emitter voltage	open base			
	BC635		–	45	V
	BC637		–	60	V
	BC639		–	80	V
I_{CM}	peak collector current		–	1.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	0.83	W
h_{FE}	DC current gain	I_C = 150 mA; V_{CE} = 2 V	40	250	
f_T	transition frequency	I_C = 50 mA; V_{CE} = 5 V; f = 100 MHz	100	–	MHz

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC635		–	45	V
	BC637		–	60	V
	BC639		–	100	V
V_{CEO}	collector-emitter voltage	open base			
	BC635		–	45	V
	BC637		–	60	V
	BC639		–	80	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	1	A
I_{CM}	peak collector current		–	1.5	A
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	0.83	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	150	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 30 V	–	100	nA
		I_E = 0; V_{CB} = 30 V; T_j = 150 °C	–	10	µA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 5 V	–	100	nA
h_{FE}	DC current gain	V_{CE} = 2 V; see Fig.2			
		I_C = 5 mA	40	–	
		I_C = 150 mA	40	250	
		I_C = 500 mA	25	–	
h_{FE}	DC current gain	I_C = 150 mA; V_{CE} = 2 V; see Fig.2			
	BC635-10; BC637-10; BC639-10		63	160	
	BC635-16; BC637-16; BC639-16		100	250	
V_{CEsat}	collector-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA	–	500	mV
V_{BE}	base-emitter voltage	I_C = 500 mA; V_{CE} = 2 V	–	1	V
f_T	transition frequency	I_C = 50 mA; V_{CE} = 5 V; f = 100 MHz	100	–	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	$\lvert I_C \rvert$ = 150 mA; $\lvert V_{CE} \rvert$ = 2 V	–	1.6	

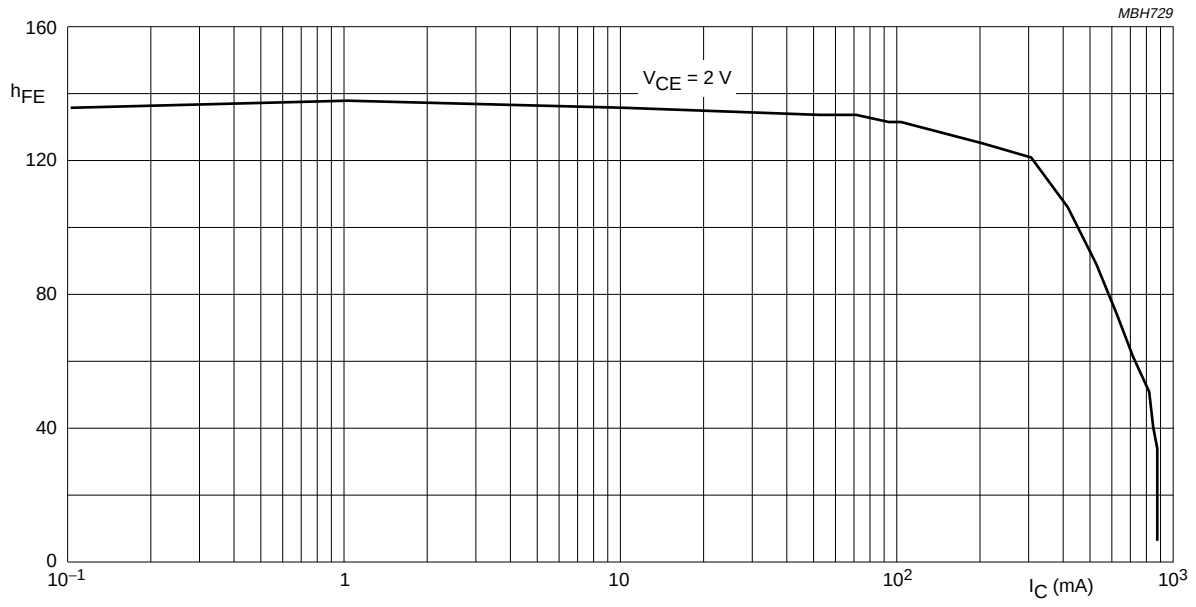
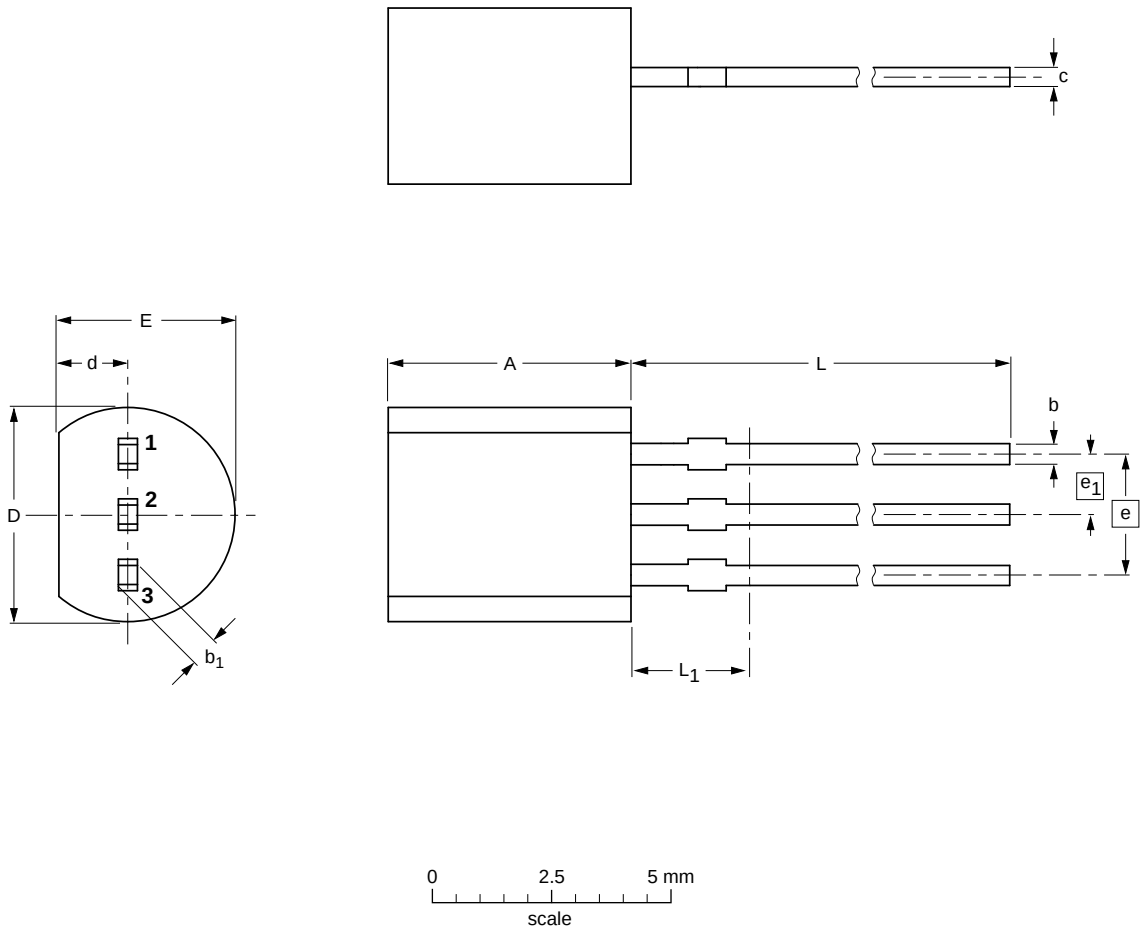


Fig.2 DC current gain; typIcal values.

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1(1)
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT54		TO-92	SC-43			97-02-28

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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